

MOSFETs Silicon N-channel MOS (U-MOSVIII-H)

# XPH3R206NC

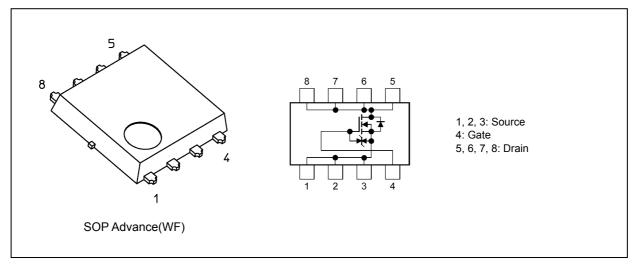
#### 1. Applications

- · Automotive
- · Motor Drivers
- · Switching Voltage Regulators

#### 2. Features

- (1) AEC-Q101 qualified
- (2) Small, thin package
- (3) Low drain-source on-resistance:  $R_{DS(ON)} = 2.6 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (4) Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 60 \text{ V)}$
- (5) Enhancement mode:  $V_{th}$  = 1.5 to 2.5 V ( $V_{DS}$  = 10 V,  $I_D$  = 0.5 mA)

#### 3. Packaging and Internal Circuit





#### 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteris	Symbol	Rating	Unit		
Drain-source voltage			$V_{DSS}$	60	V
Gate-source voltage			$V_{GSS}$	±20	
Drain current (DC)		(Note 1)	I <sub>D</sub>	70	Α
Drain current (pulsed)		(Note 1)	I <sub>DP</sub>	210	
Power dissipation	(T <sub>c</sub> = 25 °C)		$P_{D}$	132	W
Power dissipation	(t = 10 s)	(Note 2)	]	3.0	
Power dissipation	(t = 10 s)	(Note 3)	1	0.96	
Single-pulse avalanche energy		(Note 4)	E <sub>AS</sub>	147	mJ
Single-pulse avalanche current			I <sub>AS</sub>	70	Α
Channel temperature		(Note 5)	T <sub>ch</sub>	175	°C
Storage temperature		(Note 5)	T <sub>stg</sub>	-55 to 175	

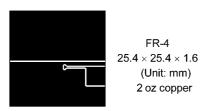
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

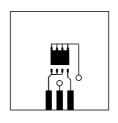
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal impedance	(T <sub>c</sub> = 25 °C)		Z <sub>th(ch-c)</sub>	1.13	°C/W
Channel-to-ambient thermal impedance	(t = 10 s)	(Note 2)	Z <sub>th(ch-a)</sub>	50	
Channel-to-ambient thermal impedance	(t = 10 s)	(Note 3)	Z <sub>th(ch-a)</sub>	156	

- Note 1: Ensure that the channel temperature does not exceed 175 °C.
- Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1
- Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2
- Note 4:  $V_{DD}$  = 48 V,  $T_{ch}$  = 25 °C (initial), L = 23.1  $\mu$ H,  $R_G$  = 25  $\Omega$ ,  $I_{AS}$  = 70 A
- Note 5: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.





FR-4  $25.4 \times 25.4 \times 1.6$  (Unit: mm) 2 oz copper

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

## 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	60	_	_	٧
	V <sub>(BR)DSX</sub>	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	40	_	_	
Gate threshold voltage	$V_{th}$	$V_{DS} = 10 \text{ V}, I_{D} = 0.5 \text{ mA}$	1.5	_	2.5	
Drain-source on-resistance	R <sub>DS(ON)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 35 \text{ A}$	_	3.9	6.2	mΩ
		$V_{GS}$ = 10 V, $I_D$ = 35 A		2.6	3.2	

## 6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	4180	_	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	180	_	
Output capacitance	C <sub>oss</sub>		_	2050	_	
Gate resistance	r <sub>g</sub>		_	2.5	5.0	Ω
Switching time (rise time)	t <sub>r</sub>	See Fig. 6.2.1	_	20	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	40	_	
Switching time (fall time)	t <sub>f</sub>		_	19	_	
Switching time (turn-off time)	t <sub>off</sub>		_	88	_	

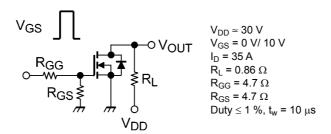


Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 48 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 70 \text{ A}$	-	65	1	nC
Gate-source charge 1	Q <sub>gs1</sub>			17		
Gate-drain charge	$Q_{gd}$			10	_	

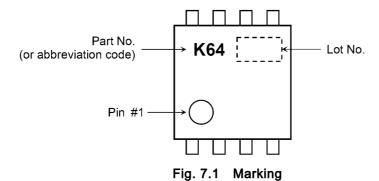
### 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (N	ote 6)	I <sub>DRP</sub>	_	_	_	210	Α
Diode forward voltage		$V_{DSF}$	I <sub>DR</sub> = 70 A, V <sub>GS</sub> = 0 V	_	_	-1.2	V

Note 6: Ensure that the channel temperature does not exceed 175 °C.



## 7. Marking





#### 8. Characteristics Curves (Note)

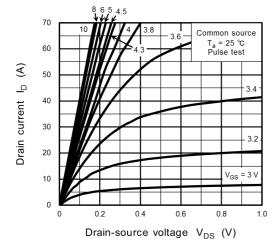


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

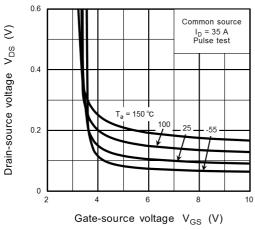


Fig. 8.3 V<sub>DS</sub> - V<sub>GS</sub>

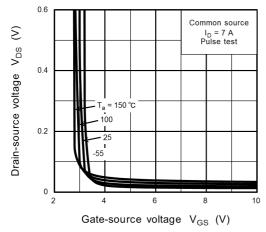


Fig. 8.5 VDS - VGS

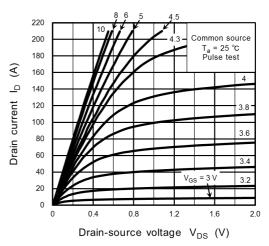


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

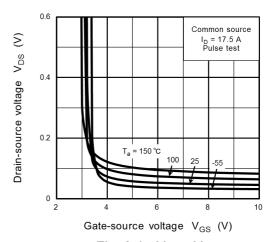


Fig. 8.4 VDS - VGS

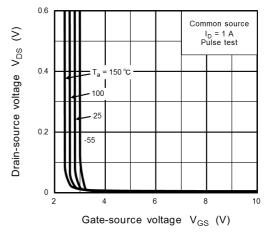


Fig. 8.6  $V_{DS} - V_{GS}$ 



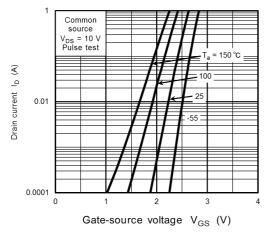


Fig. 8.7 ID - VGS

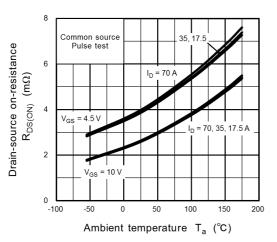


Fig. 8.9 R<sub>DS(ON)</sub> - T<sub>a</sub>

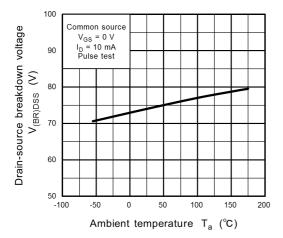


Fig. 8.11 V<sub>(BR)DSS</sub> - T<sub>a</sub>

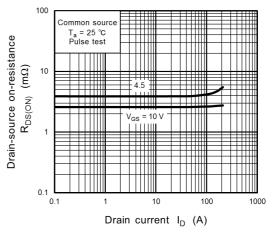


Fig. 8.8 R<sub>DS(ON)</sub> - I<sub>D</sub>

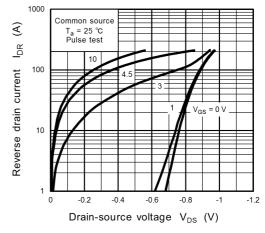


Fig. 8.10 I<sub>DR</sub> - V<sub>DS</sub>

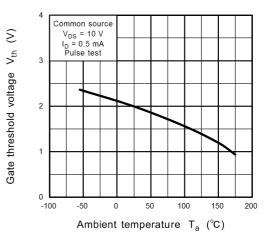


Fig. 8.12 V<sub>th</sub> - T<sub>a</sub>



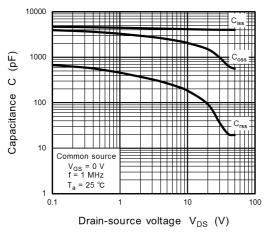


Fig. 8.13 Capacitance - V<sub>DS</sub>

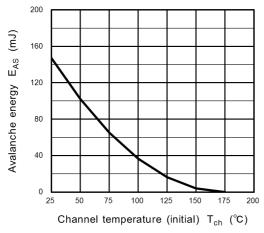


Fig. 8.15 E<sub>AS</sub> - T<sub>ch</sub>(Guaranteed Maximum)

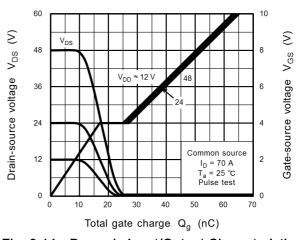


Fig. 8.14 Dynamic Input/Output Characteristics

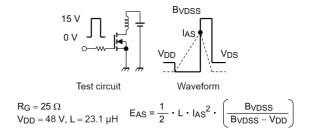


Fig. 8.16 Test Circuit/Waveform



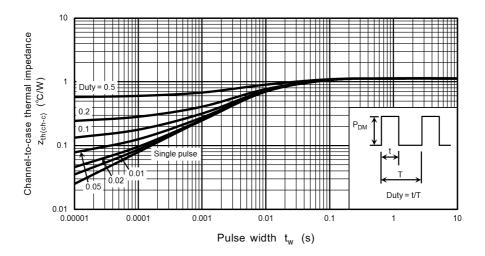
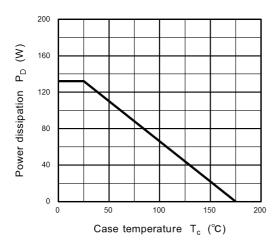


Fig. 8.17  $z_{th(ch-c)} - t_w$  (Guaranteed Maximum)



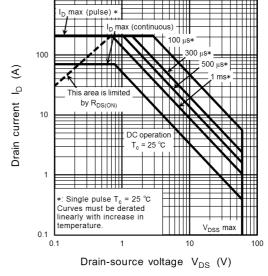


Fig. 8.18 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

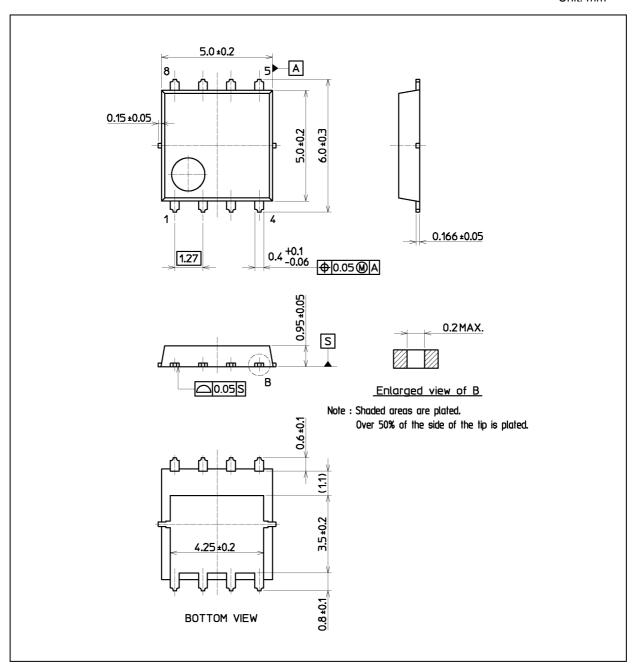
Fig. 8.19 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



#### **Package Dimensions**

Unit: mm



Weight: 0.080 g (typ.)

Package Name(s)
TOSHIBA: 2-5Q4A
Nickname: SOP Advance(WF)



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